**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: Ptot = 980 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM

# 3. Applications

- LED driver
- Power management
- · High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max  | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | -20  | V    |
| $V_{GS}$          | gate-source voltage              |   |     | -8  | -   | 8    | V    |
| I <sub>D</sub>    | drain current                    | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$ | [1] | -   | -   | -5.6 | Α    |
| Static characte   | Static characteristics           |   |     |     |     |      |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 \text{ °C}$  |     | -   | 27  | 32   | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | G      | gate        | <u></u> 3          | D<br>I         |
| 2   | S      | source      |                    |                |
| 3   | D      | drain       | 1                  | G S 017aaa259  |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |  |  |
|-------------|----------|--|---------|--|--|
|             | Name     | Description                              | Version |  |  |
| PMV27UPE    | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| PMV27UPE    | %KD              |

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |            | Min | Max  | Unit |
|------------------|-------------------------|---|------------|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>j</sub> = 25 °C                              |            | -   | -20  | V    |
| $V_{GS}$         | gate-source voltage     |   |            | -8  | 8    | V    |
| I <sub>D</sub>   | drain current           | $V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; $t \le 5$ s   | [1]        | -   | -5.6 | Α    |
|                  |                         | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C  | [1]        | -   | -4.5 | Α    |
|                  |                         | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C | [1]        | -   | -2.8 | Α    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs    |            | -   | -18  | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                            | <u>[2]</u> | -   | 490  | mW   |

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| Symbol             | Parameter            | Conditions               |     | Min | Max  | Unit |
|--------------------|----------------------|--------------------------|-----|-----|------|------|
|                    |                      |                          | [1] | -   | 980  | mW   |
|                    |                      | T <sub>sp</sub> = 25 °C  |     | -   | 4150 | mW   |
| T <sub>j</sub>     | junction temperature |                          |     | -55 | 150  | °C   |
| T <sub>amb</sub>   | ambient temperature  |                          |     | -55 | 150  | °C   |
| T <sub>stg</sub>   | storage temperature  |                          |     | -65 | 150  | °C   |
| Source-drain diode |                      |                          |     |     |      |      |
| I <sub>S</sub>     | source current       | T <sub>amb</sub> = 25 °C | [1] | -   | -1.2 | Α    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

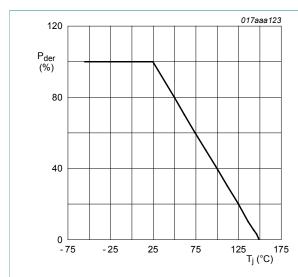


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

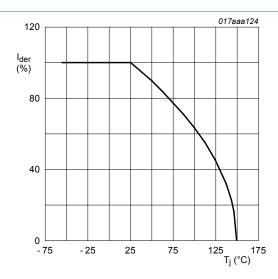


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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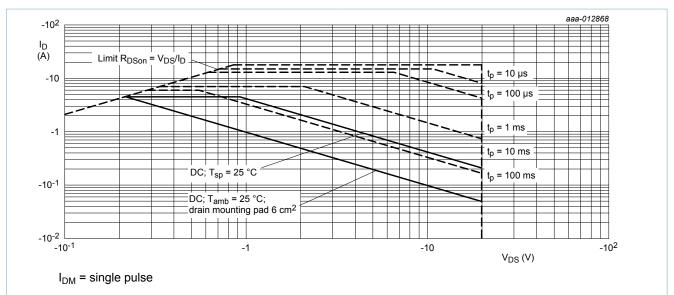


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol   | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
|--|--|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistar from junction to ambient | thermal resistance                               |                      | [1] | -   | 222 | 255 | K/W  |
|  | _  |                      | [2] | -   | 111 | 128 | K/W  |
|  | ambient  | in free air; t ≤ 5 s | [2] | -   | 74  | 85  | K/W  |
| R <sub>th(j-sp)</sub>  | thermal resistance from junction to solder point |                      |     | -   | 25  | 30  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

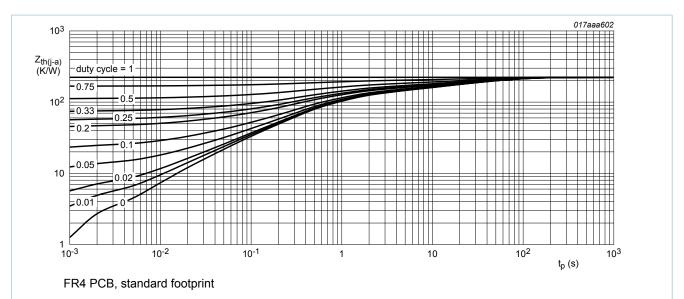


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

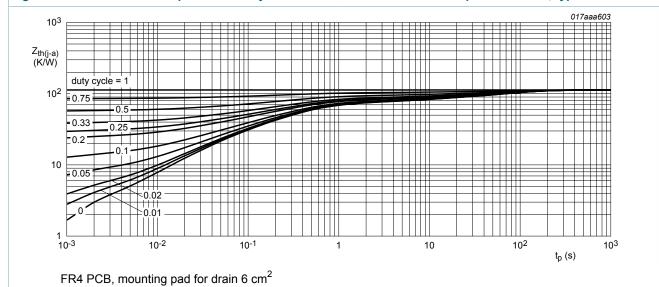


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

Table 7. Characteristics

| Symbol              | Parameter                         | Conditions   | Min   | Тур  | Max   | Unit |
|---------------------|-----------------------------------|--|-------|------|-------|------|
| Static chara        | acteristics                       |  | '     |      |       |      |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                              | -20   | -    | -     | V    |
| $V_{GSth}$          | gate-source threshold voltage     | $I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                  | -0.45 | -0.7 | -0.95 | V    |
| I <sub>DSS</sub>    | drain leakage current             | V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -     | -    | -1    | μA   |
| I <sub>GSS</sub>    | gate leakage current              | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -     | -    | 10    | μA   |
|                     |                                   | V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -     | -    | -10   | μA   |
|                     |                                   | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -     | -    | 5     | μA   |
|                     |                                   | $V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                           | -     | -    | -5    | μA   |
| R <sub>DSon</sub>   | drain-source on-state             | $V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 \text{ °C}$       | -     | 27   | 32    | mΩ   |
| resistance          | resistance                        | V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 150 °C | -     | 40   | 48    | mΩ   |
|                     |                                   | $V_{GS}$ = -2.5 V; $I_D$ = -3.8 A; $T_j$ = 25 °C                           | -     | 38   | 45    | mΩ   |
|                     |                                   | $V_{GS}$ = -1.8 V; $I_D$ = -3 A; $T_j$ = 25 °C                             | -     | 50   | 63    | mΩ   |
| g <sub>fs</sub>     | forward transconductance          | $V_{DS}$ = -10 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C                          | -     | 15   | -     | S    |
| R <sub>G</sub>      | gate resistance                   | f = 1 MHz  | -     | 10.7 | -     | Ω    |
| Dynamic ch          | naracteristics                    |  |       |      |       |      |
| Q <sub>G(tot)</sub> | total gate charge                 | $V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V;                     | -     | 14.7 | 22.1  | nC   |
| $Q_{GS}$            | gate-source charge                | T <sub>j</sub> = 25 °C   | -     | 2.6  | -     | nC   |
| $Q_{GD}$            | gate-drain charge                 |  | -     | 2.5  | -     | nC   |
| C <sub>iss</sub>    | input capacitance                 | $V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;                               | -     | 1820 | -     | pF   |
| C <sub>oss</sub>    | output capacitance                | T <sub>j</sub> = 25 °C   | -     | 208  | -     | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance      |  | -     | 146  | -     | pF   |
| t <sub>d(on)</sub>  | turn-on delay time                | $V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V;                     | -     | 11   | -     | ns   |
| t <sub>r</sub>      | rise time                         | $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$                                    | -     | 30   | -     | ns   |
| $t_{\text{d(off)}}$ | turn-off delay time               |  | -     | 83   | -     | ns   |
| t <sub>f</sub>      | fall time                         |  | -     | 39   | -     | ns   |
| Source-dra          | in diode                          |  | '     |      |       | ,    |
| V <sub>SD</sub>     | source-drain voltage              | $I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$          | -     | -0.7 | -1.2  | V    |
|                     |                                   | i l  |       |      |       |      |

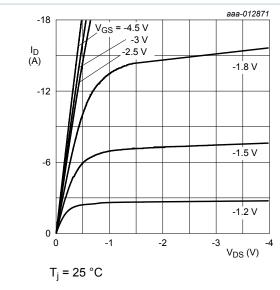


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

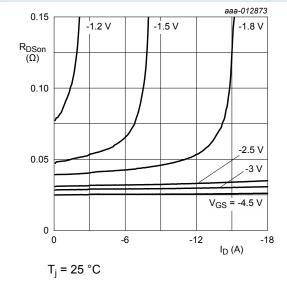


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

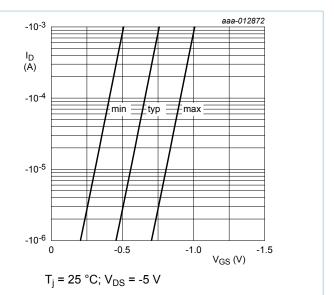


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

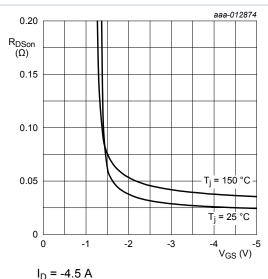


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

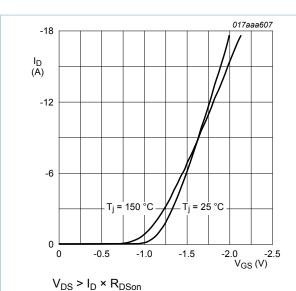


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

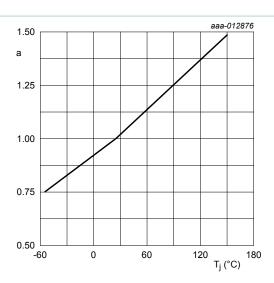


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

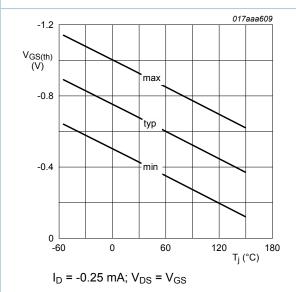
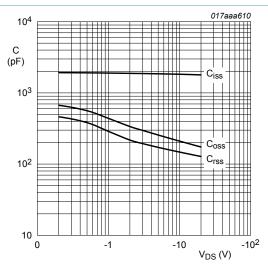


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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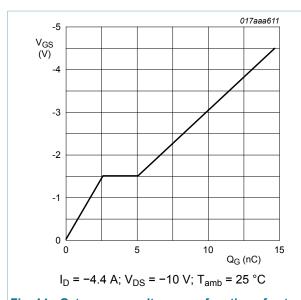


Fig. 14. Gate-source voltage as a function of gate charge; typical values

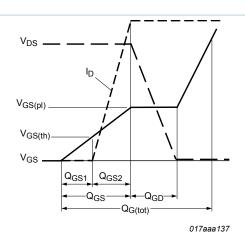


Fig. 15. MOSFET transistor: Gate charge waveform definitions

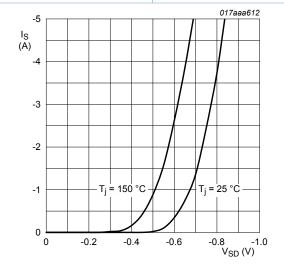
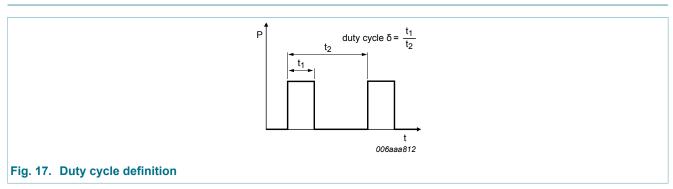


Fig. 16. Source current as a function of source-drain voltage; typical values

# 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

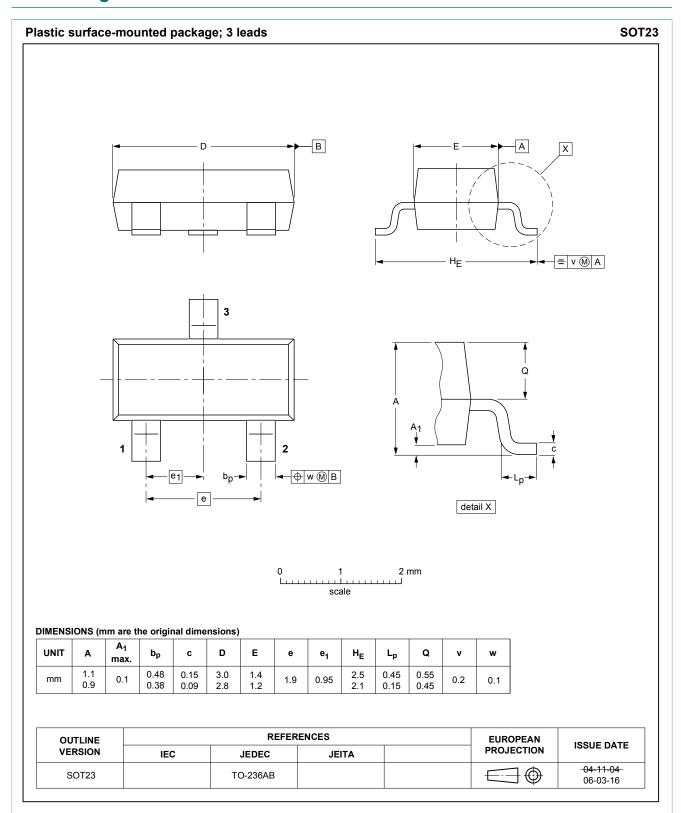
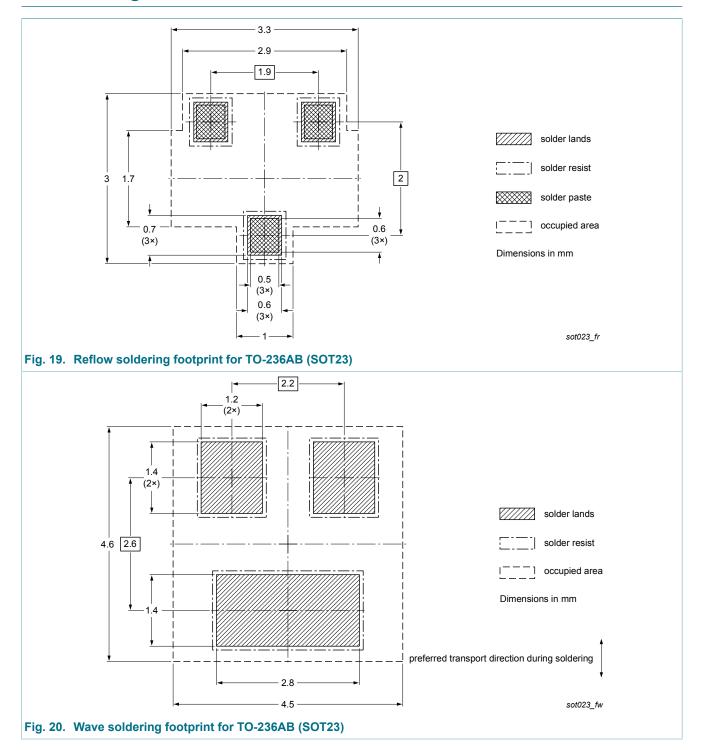


Fig. 18. Package outline TO-236AB (SOT23)

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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV27UPE v.1  | 20140515     | Product data sheet | -             | -          |

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## 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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